

5th Generation CoolSiC™ 1200V Schottky Diode

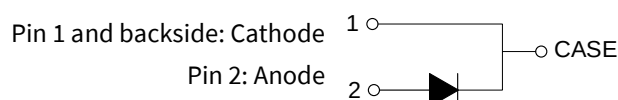
SiC Diode

Features

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current / no forward recovery
- Temperature independent switching behaviour
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Pb-free lead plating; RoHS compliant



Pin definition



Potential applications

- Drives
- Industrial power supplies: Industrial UPS
- Solar central inverters and Solar string inverter

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Description

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability
- Related Links: www.infineon.com/SiC



Key performance parameters

Type	V_{DC}	I_F	Q_C	$T_{vj,max}$	Marking	Package
IDK20G120C5	1200 V	20 A	82nC	175°C	D2012C5	PG-TO263-2

Table of contents

Features	1
Potential applications	1
Product validation	1
Description	1
Key performance parameters.....	1
Table of contents.....	2
1 Maximum ratings	3
2 Thermal resistances	5
3 Electrical Characteristics	6
4 Electrical Characteristics Diagrams	7
5 Package Drawing	10
Revision history.....	11

Maximum ratings

1 Maximum ratings

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage $T_C \geq 25^\circ\text{C}$	V_{RRM}	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 145^\circ\text{C}$, D=1 $T_C = 135^\circ\text{C}$, D=1 $T_C = 25^\circ\text{C}$, D=1	I_F	20 27 56	A
Surge repetitive forward current, sine halfwave ¹ $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$ $T_C=100^\circ\text{C}$, $t_p=10\text{ms}$	$I_{F,RM}$	80 60	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$ $T_C=150^\circ\text{C}$, $t_p=10\text{ms}$	$I_{F,SM}$	198 168	A
Non-repetitive peak forward current $T_C = 25^\circ\text{C}$, $t_p=10\text{ }\mu\text{s}$	$I_{F,max}$	1200	A
i^2t value $T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$ $T_C = 150^\circ\text{C}$, $t_p=10\text{ ms}$	$\int i^2 dt$	195 140	A ² s
Diode dv/dt ruggedness $V_R=0\ldots 960\text{ V}$	dv/dt	80	V/ns
Power dissipation for $R_{th(j-c,max)}$ $T_C = 25^\circ\text{C}$	P_{tot}	330	W

¹ Not subject to production test. The test was performed with 20000 pulses (two consecutive half-wave rectified sines with 10 ms period).

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Maximum ratings

Operating temperature	T_{vj}	-55...175	°C
Storage temperature	T_{stg}	-55...150	°C
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STD-020)	T_{sold}	260	°C

2 Thermal resistances

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Characteristic						
Diode thermal resistance, junction – case	R _{th(j-c)}		-	0.35	0.46	K/W
Thermal resistance, junction – ambient	R _{th(j-a)}	Leaded	-	-	62	K/W

3 Electrical Characteristics

Static Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}	$T_{vj} = 25^{\circ}\text{C}$, $I_R=50\mu\text{A}$	1200	-	-	V
Diode forward voltage	V_F	$I_F=20\text{A}$, $T_{vj}=25^{\circ}\text{C}$	-	1.5	1.8	V
		$I_F=20\text{A}$, $T_{vj}=150^{\circ}\text{C}$	-	2.0	-	
Reverse current	I_R	$V_R=1200\text{V}$, $T_{vj}=25^{\circ}\text{C}$	-	8.5	123	μA
		$V_R=1200\text{V}$, $T_{vj}=150^{\circ}\text{C}$	-	44	-	

Dynamic Characteristics, at $T_{vj}=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Total capacitive charge	Q_C	$V_R = 800\text{V}$, $T_{vj}=150^{\circ}\text{C}$ $Q_C = \int_0^{V_R} C(V)dV$	-	82	-	nC
Total Capacitance	C	$V_R=1\text{V}$, $f=1\text{MHz}$	-	1050	-	pF
		$V_R=400\text{V}$, $f=1\text{MHz}$	-	74	-	
		$V_R=800\text{V}$, $f=1\text{MHz}$	-	59	-	

4 Electrical Characteristics Diagrams

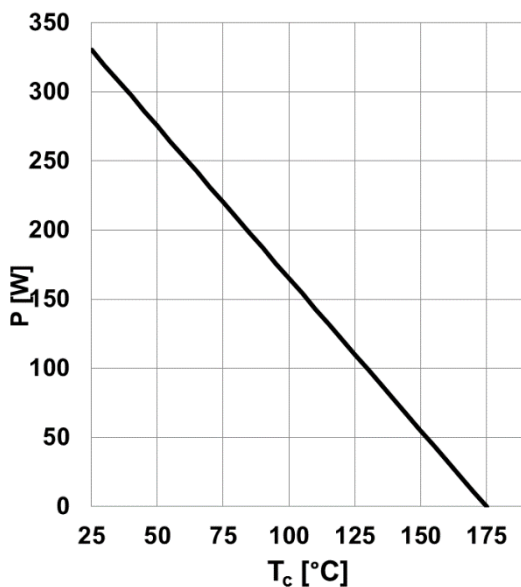


Figure 1. Power dissipation as function of case temperature, $P_{\text{tot}}=f(T_c)$, $R_{\text{th(j-c),max}}$

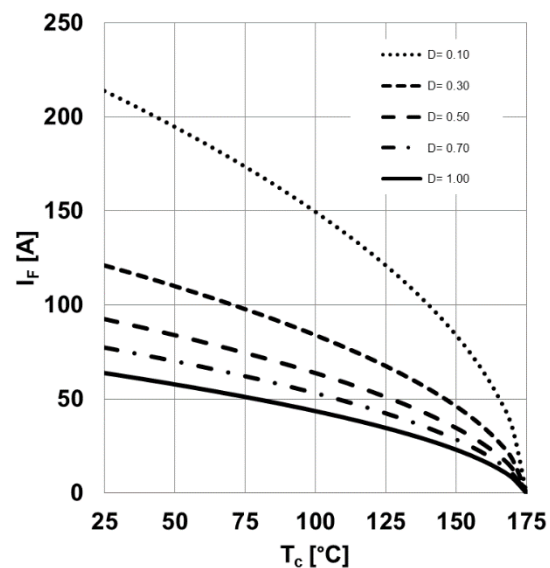


Figure 2. Diode forward current as function of temperature, parameter: $T_{vj} \leq 175^\circ\text{C}$, $R_{\text{th(j-c),max}}$, D =duty cycle, V_{th} , R_{diff} @ $T_{vj}=175^\circ\text{C}$

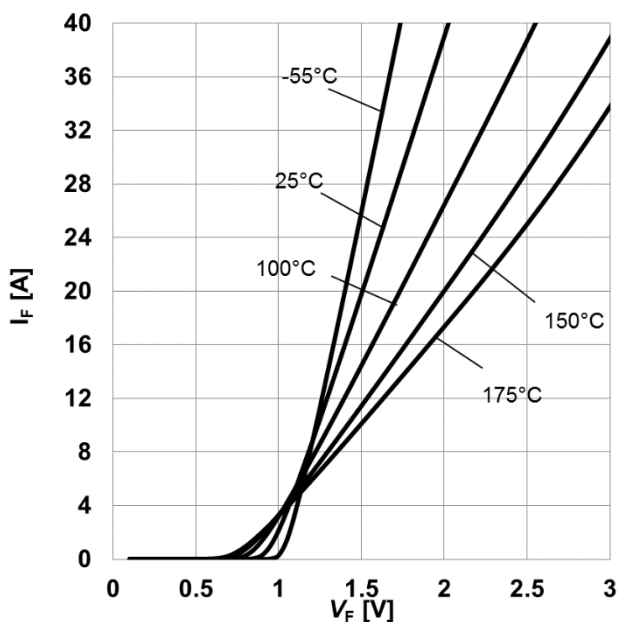


Figure 3. Typical forward characteristics, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_{vj}

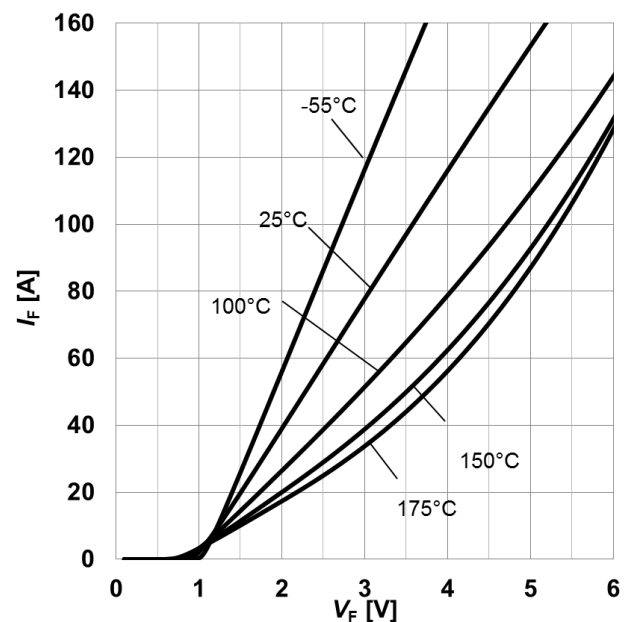


Figure 4. Typical forward characteristics in surge current, $I_F=f(V_F)$, $t_p=10\text{ }\mu\text{s}$, parameter: T_{vj}

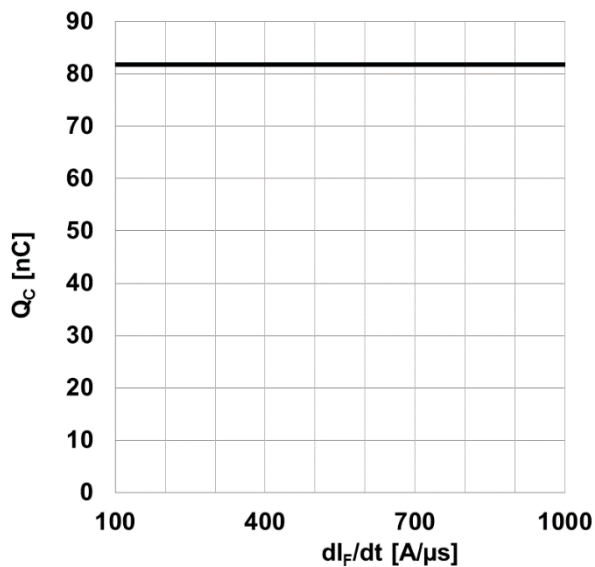


Figure 5. Typical capacitive charge as function of current slope, $Q_c=f(diF/dt)$, $T_{vj}=150^{\circ}\text{C}$

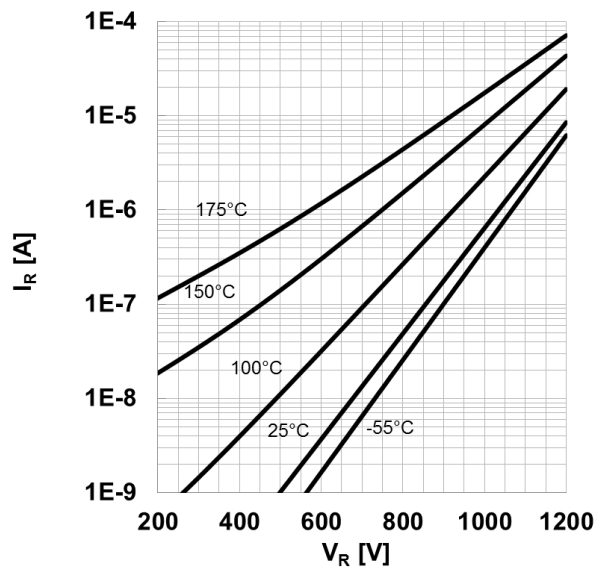


Figure 6. Typical reverse characteristics, $I_R=f(V_R)$, parameter: T_{vj}

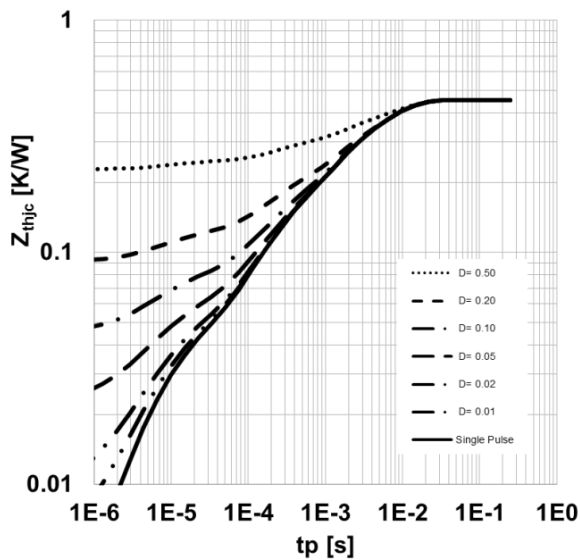


Figure 7. Max. transient thermal impedance, $Z_{th,j-c}=f(t_p)$, parameter: $D=t_p/T$

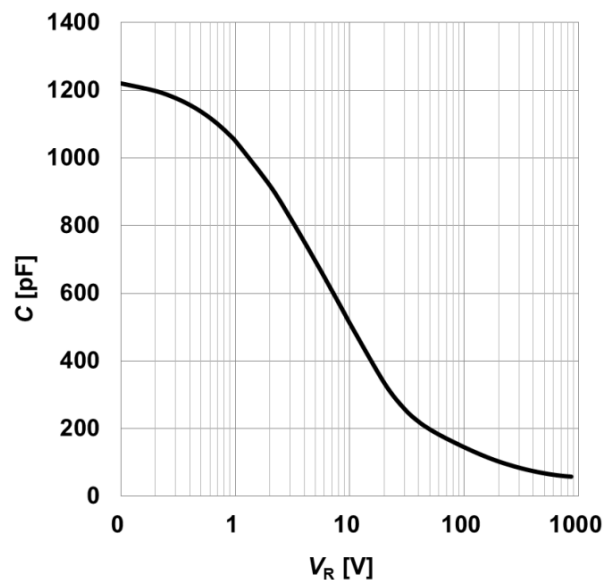


Figure 8. Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_{vj}=25^{\circ}\text{C}$; $f=1\text{ MHz}$

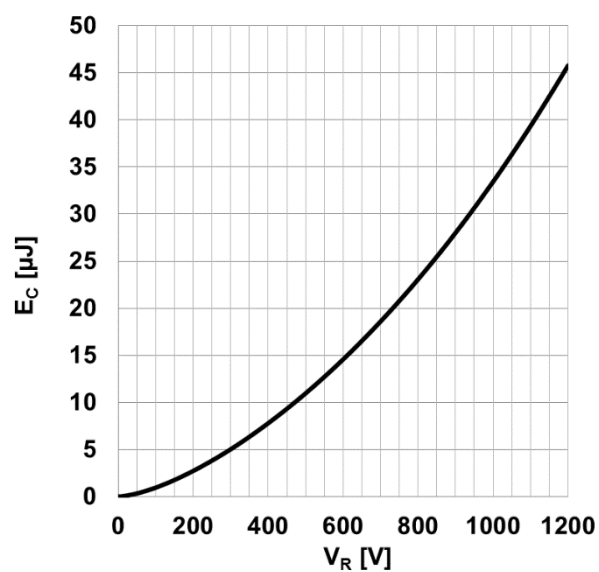


Figure 9. Typical capacitively stored energy as function of reverse voltage, $E_C=f(V_R)$

Revision history

Document version	Date of release	Description of changes
V 1.0	2019-01-25	Preliminary Datasheet
V 2.0	2019-10-28	Final Datasheet

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Email: erratum@infineon.com

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